# • Electrical characteristics $(T_a = 25^{\circ}C)$

Danamatan	Symbol Conditions	Values			Unit		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Collector-emitter voltage	V <sub>CEO(SUS)</sub>	I <sub>C</sub> = -3A, I <sub>B</sub> = -300mA L = 1mH	-60	-	-	V	
Collector-base breakdown voltage	BV <sub>CBO</sub>	I <sub>C</sub> = -50μA	-100	-	-	V	
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> = -1mA	-60	-	-	V	
Emitter-base breakdown voltage	BV <sub>EBO</sub>	I <sub>E</sub> = -50μA	-5	-	-	V	
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -100V	-	-	-10	μA	
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V	-	-	-10	μA	
Callactor amitter acturation valtage	V <sub>CE(sat)</sub> 1	I <sub>C</sub> = -3A, I <sub>B</sub> = -150mA	-	-	-300	mV	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub> 2*4	I <sub>C</sub> = -4A, I <sub>B</sub> = -200mA	-	-	-500	mV	
Base-emitter saturation voltage	V <sub>BE(sat)</sub> 1*4	I <sub>C</sub> = -3A, I <sub>B</sub> = -150mA	-	-	-1.2	V	
	V <sub>BE(sat)</sub> 2*4	I <sub>C</sub> = -4A, I <sub>B</sub> = -200mA	-	-	-1.5	V	
DC current gain	h <sub>FE</sub> 1*4	V <sub>CE</sub> = -2V, I <sub>C</sub> = -1A	82	150	270	_	
	h <sub>FE</sub> 2*4	$V_{CE} = -2V, I_{C} = -3A$	40	-	-		
Transition frequency	f <sub>T</sub> *4	V <sub>CE</sub> = -10V, I <sub>E</sub> = 0.5A, f = 30MHz	-	80	-	MHz	
Output capacitance	C <sub>ob</sub>	$V_{CB} = -10V, I_{E} = 0A,$ f = 1MHz	-	130	-	pF	
Turn-on delay time	t <sub>on</sub>	I <sub>C</sub> = -3A, I <sub>B1</sub> = -150mA,	-	-	0.3	μs	
Storage time	t <sub>stg</sub>	$I_{B2} = 150 \text{mA},$ $V_{CC} \simeq -30 \text{V},$	1	1	1.5	μs	
Fall time	t <sub>f</sub>	$R_L = 10\Omega$ See test circuit	-	-	0.3	μs	

# hFE values are calssified as follows:

rank	Р	Q	-	-	-
h <sub>FE</sub> 1	82-180	120-270	-	-	-

\*1 t=100ms

\*2 Ta=25℃

\*3 Tc=25℃

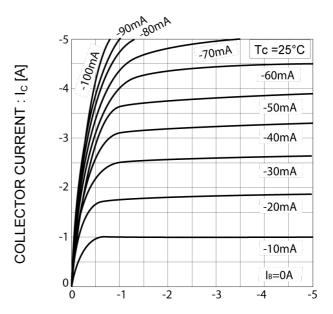
\*4 Pulsed

#### ● Electrical characteristic curves(T<sub>a</sub> = 25°C)

Fig.1 Ground Emitter Propagation Characteristics

-5 COLLECTOR CURRENT : I<sub>C</sub> [mA] VCE=-2V -2 Pulsed Ta=100°C -1 25°C -25°C -0.5 -0.2 -0.1 -0.05 -0.02 -0.01 -0.6 -0.8 -1.0 -1.2

Fig.2 Typical Output Characteristics



COLLECTOR TO EMITTER VOLTAGE: VCE [V]

Fig.3 DC Current Gain vs. Collector Current (I)

BASE TO EMITTER VOLTAGE: VBE [V]

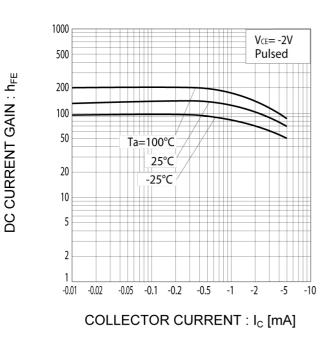
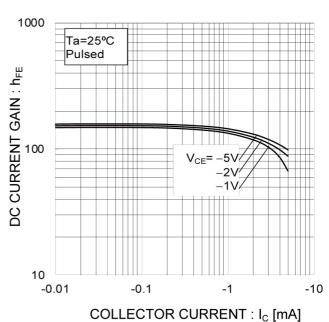


Fig.4 DC Current Gain vs. Collector Current (II)



# ● Electrical characteristic curves(T<sub>a</sub> = 25°C)

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

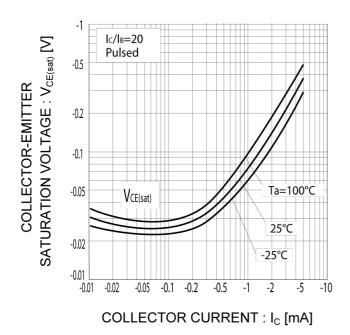


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (II)

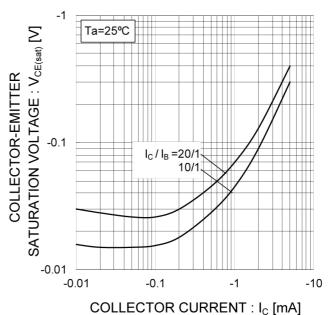


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

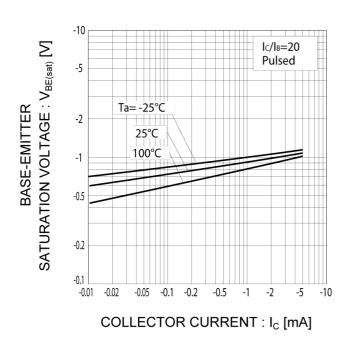
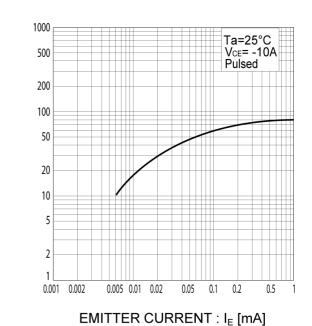


Fig.8 Gain Bandwidth Product vs. Emitter Current



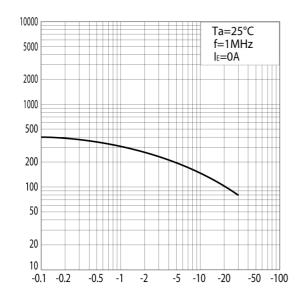
TRANSITION FREQUENCY : fr [MHz]

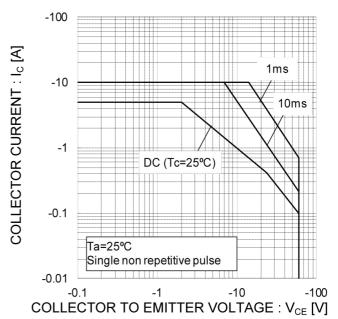
COLLECTOR OUTPUT CAPACITANCE: C<sub>ob</sub> [pF]

# ● Electrical characteristic curves(T<sub>a</sub> = 25°C)

Fig.9 Emitter Input Capacitance vs.
Emitter-Base Voltage
Collector Output Capacitance vs.
Collector-Base Voltage

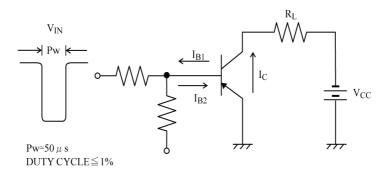
Fig.10 Safe Operating Area

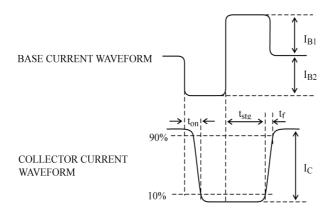




COLLECTOR-BASE VOLTAGE : V<sub>CB</sub> [V]

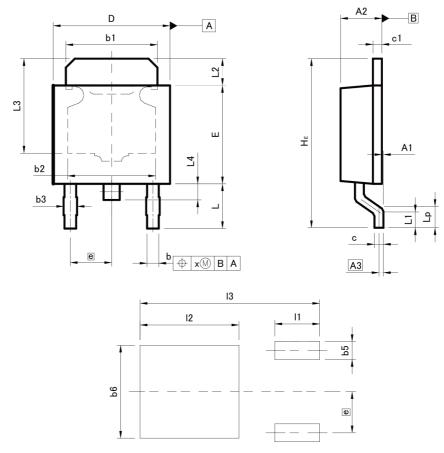
#### SWITCHING TIME TEST CIRCUIT





#### Dimensions

CPT



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
A1	0.00	0.15	0.000	0.006	
A2	2.20	2.50	0.087	0.098	
A3	0.25		0.010		
b	0.55	0.75	0.022	0.030	
b1	5.00	5.30	0.197	0.209	
b2	5.	5.00		97	
b3	0.75		0.030		
С	0.40	0.60	0.016	0.024	
c1	0.40	0.60	0.016	0.024	
D	6.30	6.70	0.248	0.264	
Е	5.40	5.80	0.213	0.228	
е	2.30		0.091		
HE	9.00	10.00	0.354	0.394	
L	2.20	2.80	0.087	0.110	
L1	0.80	1.40	0.031	0.055	
L2	1.20	1.80	0.047	0.071	
L3	5.30		0.209		
L4	0.90		0.035		
Lp	1.00	1.60	0.039	0.063	
Х	_	0.25	_	0.010	

DIM	MILIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
b5	-	1.00	-	0.04	
b6	-	5.20	-	0.205	
l1	-	2.50	_	0.098	
12	_	5.50	_	0.217	
13	_	10.00	_	0.394	

Dimension in mm/inches



6/6

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